

Supporting information

Facile one-pot synthesis of defect-engineered step-scheme $\text{WO}_3/\text{g-C}_3\text{N}_4$ heterojunctions for efficient photocatalytic hydrogen production

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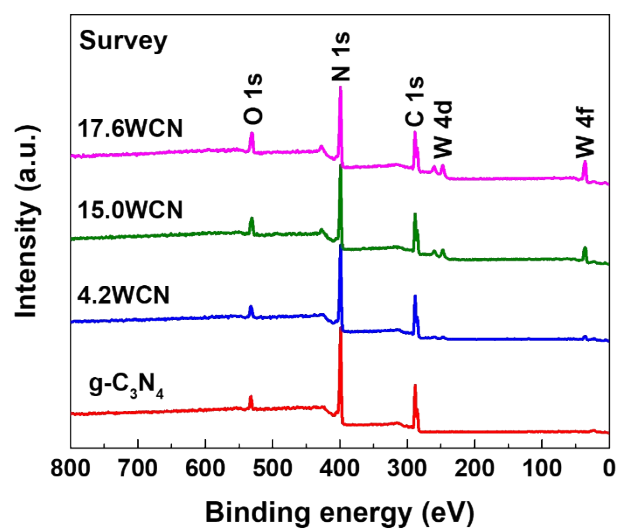


Fig. S1. XPS survey spectra of g-C₃N₄ and *n*WCN.

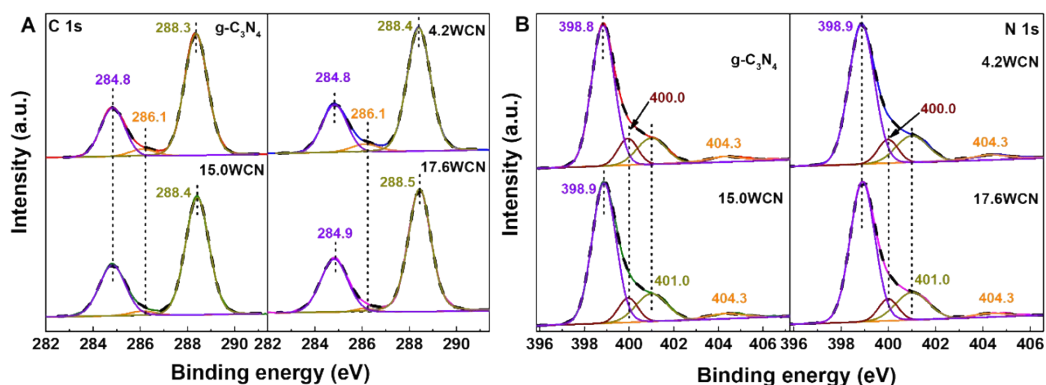


Fig. S2. XPS spectra of (A) C 1s and (B) N 1s.

The C 1s XPS spectra of $g\text{-C}_3\text{N}_4$ in Fig. S2A could be divided into three peaks at 284.8 eV, 286.1 eV and 288.3 eV, ascribing to the carbon impurities species (C-C), the C-N and sp^2 -hybridized carbon bonded to the neighboring three nitrogen atoms (N-C=N) in $g\text{-C}_3\text{N}_4$ lattice, respectively.^[1] Compared with $g\text{-C}_3\text{N}_4$, the peaks locating at about 284.8 eV and 288.3 eV in the $n\text{WCN}$ samples have a certain shift toward high binding energy. Fig. S2B displays the N 1s spectra of $g\text{-C}_3\text{N}_4$ and $n\text{WCN}$. It can be segregated into four peaks at 398.8 eV, 400.0 eV, 401.0 eV and 404.3 eV, corresponding to sp^2 -hybridized N species (C=N-C), sp^3 -hybridized tertiary N-(C)₃ groups, amino functional groups (C-N-H) and the π -excitation of C-N heterocycles, respectively.^[2, 3] The peak at 398.8 eV of $n\text{WCN}$ has a slight positive shift compared with pure $g\text{-C}_3\text{N}_4$. Combined with the C 1s XPS spectra, the shift to high binding energy indicates the existence of charge transfer between $g\text{-C}_3\text{N}_4$ and WO_3 .^[4]

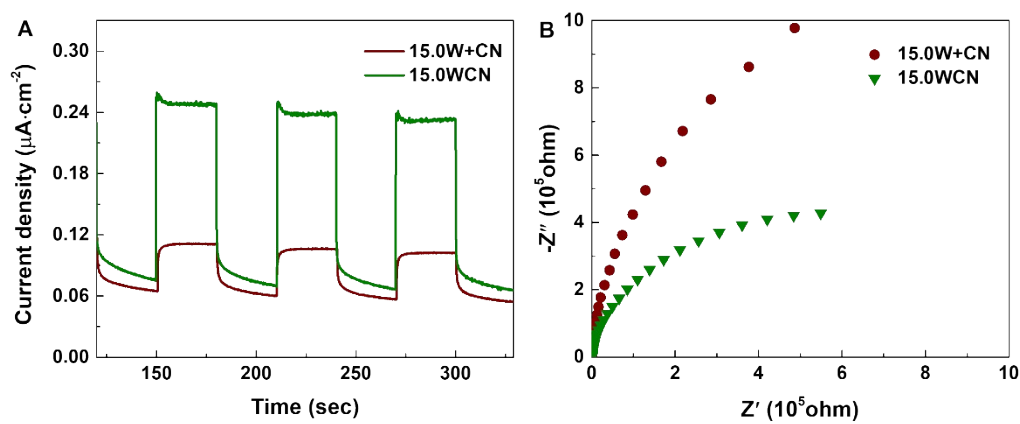


Fig. S3. (A) Transient photocurrent responses and (B) EIS Nyquist plots of 15.0W+CN and 15.0WCN.

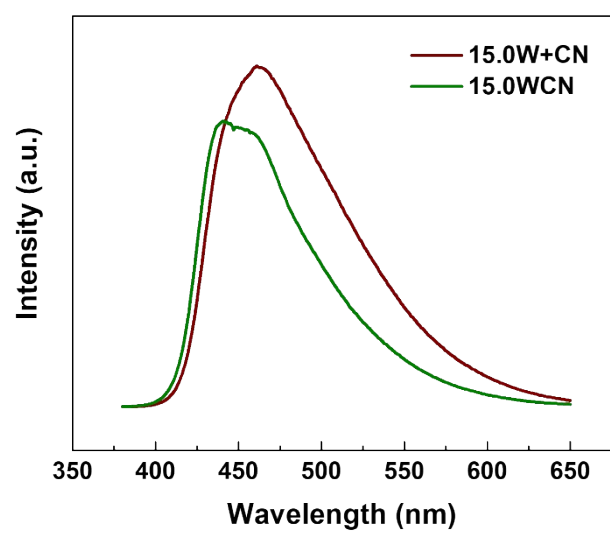


Fig. S4. Photoluminescence emission spectra of 15.0W+CN and 15.0WCN.

Table S1. The BET surface area and pore structure of the samples.

Samples	S_{BET} ($\text{m}^2 \text{g}^{-1}$)	Pore volume ($\text{cm}^3 \text{g}^{-1}$)	Pore diameter (nm)
WO_3	4.2	0.01	2.1
g- C_3N_4	14.8	0.03	4.8
4.2WCN	16.7	0.04	4.7
15.0WCN	18.8	0.03	4.7
17.6WCN	19.1	0.04	4.7

Table S2. The H₂ production rates and apparent quantum efficiencies of the samples.

Samples	H ₂ production rate (μmol h ⁻¹)	AQE (%)
g-C ₃ N ₄	5.8	1.7%
4.2WCN	11.2	3.3%
15.0WCN	24.5	7.4%
17.6WCN	12.4	3.7%

Table S3. Binding energy, peak area and relative percentage of different W species in W 4f spectra.

samples	Binding energy of W (eV)				peak area (Counts)		Percentage (%)	
	W ⁶⁺		W ⁵⁺		W ⁶⁺	W ⁵⁺	W ⁶⁺	W ⁵⁺
	4f _{5/2}	4f _{7/2}	4f _{5/2}	4f _{7/2}				
WO ₃	38.0	35.9	-	-	112734.6	-	100	0
4.2WCN	37.3	35.2	36.3	34.2	3135.0	153.6	95.3	4.7
15.0WCN	37.4	35.3	36.3	34.3	13635.3	781.8	94.6	5.4
17.6WCN	37.4	35.3	36.4	34.3	18890.6	819.4	95.8	4.2

Table S4. Binding energy, peak area and relative percentage of different O species in O 1s spectra.

samples	Binding energy of O 1s (eV)			peak area (Counts)			Percentage (%)		
	O _L	O _{OH}	O _{C-O}	O _L	O _{OH}	O _{C-O}	O _L	O _{OH}	O _{C-O}
WO ₃	530.7	531.8	-	61148.0	14720.9	-	80.6	19.4	-
4.2WCN	529.9	531.8	532.5	2263.7	4432.4	7381.9	16.1	31.5	52.4
15.0WCN	529.9	531.8	532.5	8087.6	6732.2	3749.4	43.5	36.3	20.2
17.6WCN	530.0	531.8	532.5	11673.1	6000.6	3506.7	55.1	28.3	16.6

$$\text{Equation S1: } \alpha h\nu = A(h\nu - E_g)^{\frac{2}{n}}$$

where α , $h\nu$, A and E_g are the optical absorption coefficient, the photon energy, the absorption constant and the band gap energy, respectively. The value of n is determined by the transition properties of semiconductor. The n equals to 1 for the direct transition, while the n equals to 4 for the indirect transition.^[5] Hence, the values of n are 1 and 4 for WO_3 and $g\text{-C}_3\text{N}_4$, respectively.

$$\text{Equation S2: } I_t = A \exp\left(\frac{-t}{\tau}\right) + y_0$$

$$\text{Equation S3: } I_t = A_1 \exp\left(\frac{-t}{\tau_1}\right) + A_2 \exp\left(\frac{-t}{\tau_2}\right)$$

Where the A_1 and A_2 are constants representing the weight factor. The τ_1 and τ_2 are fast decay time and slow decay time, which stem from the nonradiative recombination of photo-generated electrons at CB into the trap sites of defects and radiative recombination of the photogenerated electrons with the holes at VB, respectively.^[6] The PL lifetime of WO_3 was obtained using single exponential fitting equation (Equation S2), while the PL lifetimes of $g\text{-C}_3\text{N}_4$ and $n\text{WCN}$ were calculated using double exponential fitting equation (Equation S3). We also calculated the average fluorescence lifetime τ using the Equation S4.

$$\text{Equation S4: } \tau = A_1 \tau_1^2 + A_2 \tau_2^2 / A_1 \tau_1 + A_2 \tau_2$$

References

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